



Surface Mount Schottky Rectifier

Features

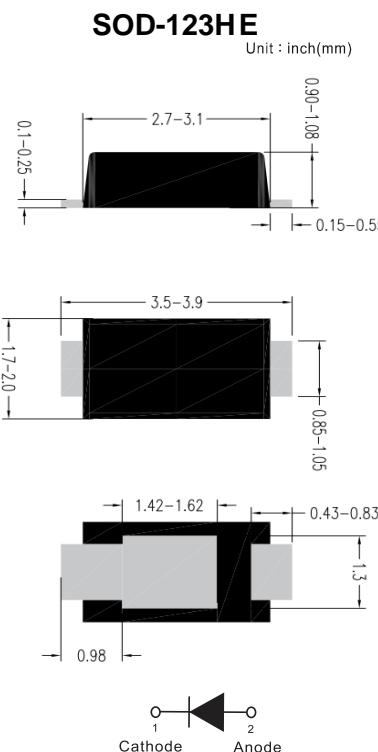
- Low profile package
- Ideal for automated placement
- Guardring for overvoltage protection
- Low power losses, high efficiency
- High forward surge capability
- AEC-Q101 qualified
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

Typical Applications

For use in low voltage high frequency inverters, freewheeling, DC/DC converters, and polarity protection applications.

Mechanical Data

- **Package:** SOD-123HE
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** Cathode line denotes the cathode end



■Maximum Ratings ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	S12HE-Q	S13HE-Q	S14HE-Q	S15HE-Q	S16HE-Q	S18HE-Q	S110HE-Q	S115HE-Q	S120HE-Q
Repetitive peak reverse voltage	VRRM	V	20	30	40	50	60	80	100	150	200
Average rectified output current @60Hz sine wave, Resistance load, T_a (FIG.1)	IO	A							1.0		
Surge(non-repetitive)forward current @60Hz half-sine wave, 1 cycle, $T_j=25^\circ\text{C}$	IFSM	A						30			
Storage temperature	Tstg	°C						-55 ~+150			
Junction temperature	T _j	°C				-55 ~+150			-55 ~+175		

■Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	S12HE-Q	S13HE-Q	S14HE-Q	S15HE-Q	S16HE-Q	S18HE-Q	S110HE-Q	S115HE-Q	S120HE-Q
Maximum instantaneous forward voltage drop per diode	VF	V	IFM=1.0A	0.50		0.65		0.80		0.85		
Maximum DC reverse current at rated DC blocking voltage per diode @ VRM=VRRM	IRRM	mA	T _a =25°C		0.10				0.05			
			T _a =100°C		10				5			



■ Thermal Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	S12HE-Q	S13HE-Q	S14HE-Q	S15HE-Q	S16HE-Q	S18HE-Q	S110HE-Q	S115HE-Q	S120HE-Q
Thermal Resistance	R _{θJ-A}	°C/W						70 ¹⁾			
	R _{θJ-L}							20 ¹⁾			

Note:

(1) Thermal resistance between junction and ambient and between junction and lead mounted on P.C.B with 3mm*3mm copper pad areas.

■ Characteristics (Typical)

FIG1:Io-TLCurve

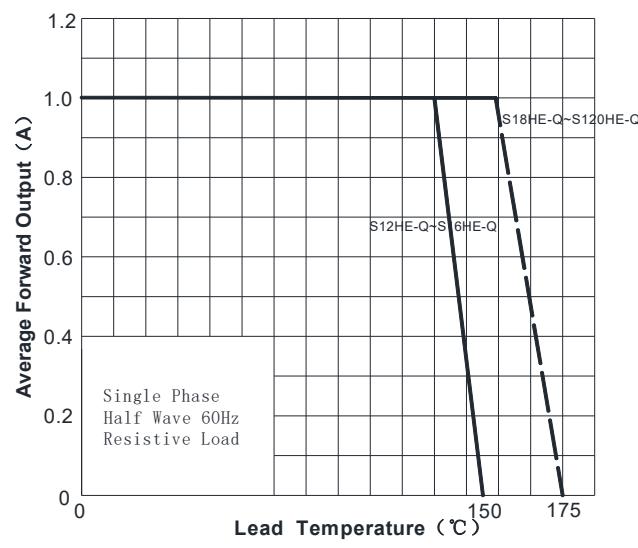


FIG2: Surge Forward Current Capability

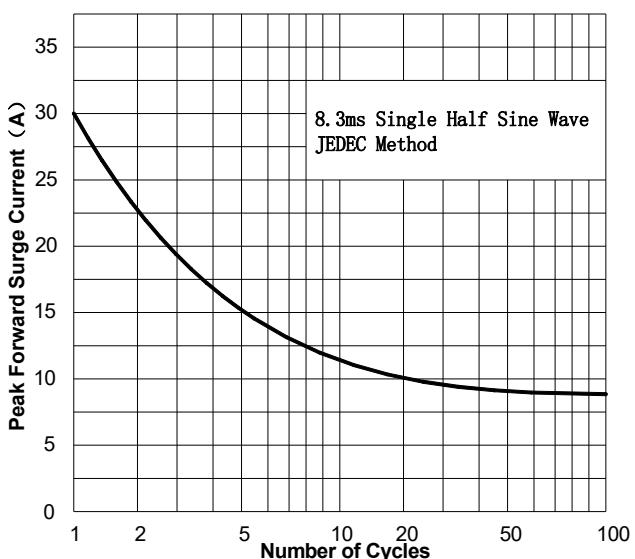


FIG3: Forward Voltage

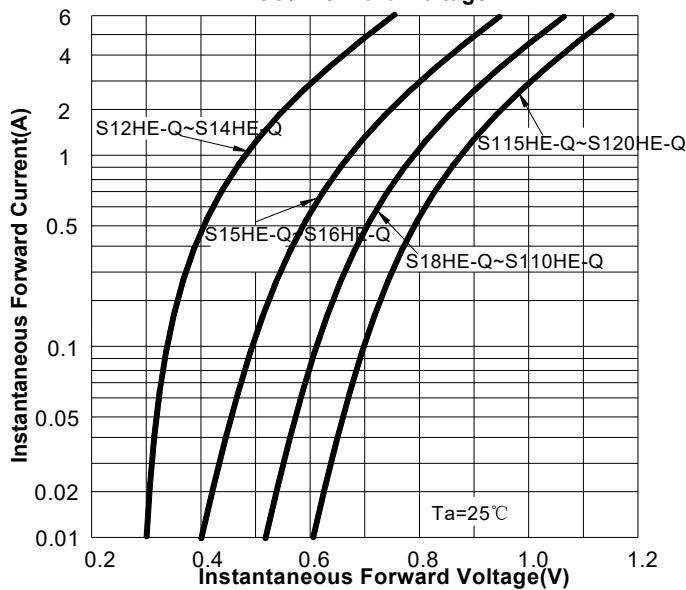


FIG4: Typical Reverse Characteristics

